

Performance

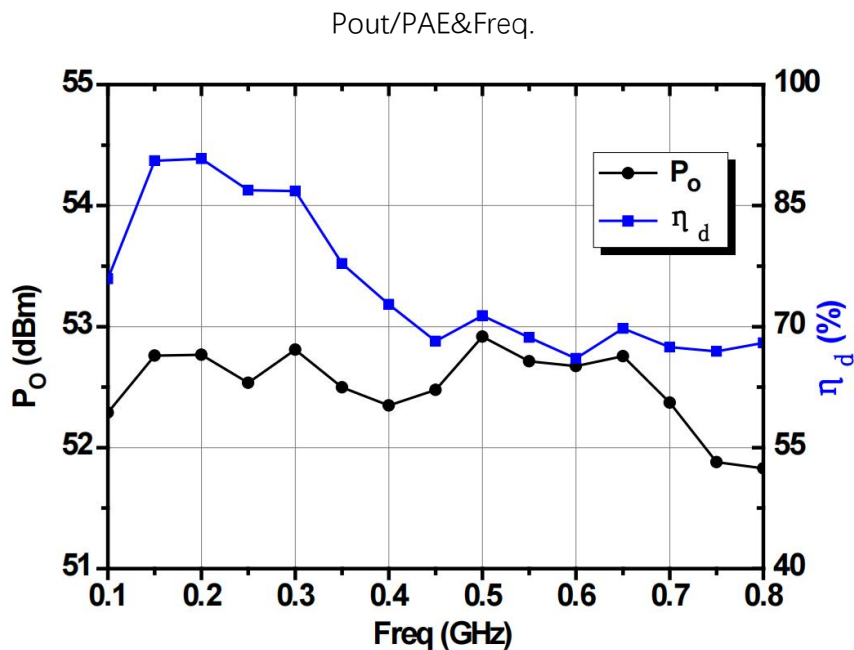
- Technology: 0.25um Power GaN HEMT
- Frequency: 0.1~0.8GHz
- Typical Pout : 52dBm(CW)
- Typical Gain: 15dB
- Typical PAE: $\geq 65\%$
- Bias: 28V/-2.6~-1.6V@1A
- Package: Metal Ceramic



Electrical Specifications ($T_A=25^\circ\text{C}$, $V_d=28\text{V}$, $I_{dQ}=1\text{A}$, $P_{in}=37\text{dBm}$, $F: 0.1\sim 0.8\text{GHz}$)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	52	-	dBm
Gp	Power Gain	-	15	-	dB
η_{add}	Power Added Efficiency	65	-	-	%
ΔGp	Gain Flatness	-	-	± 0.5	dB

Test Curves

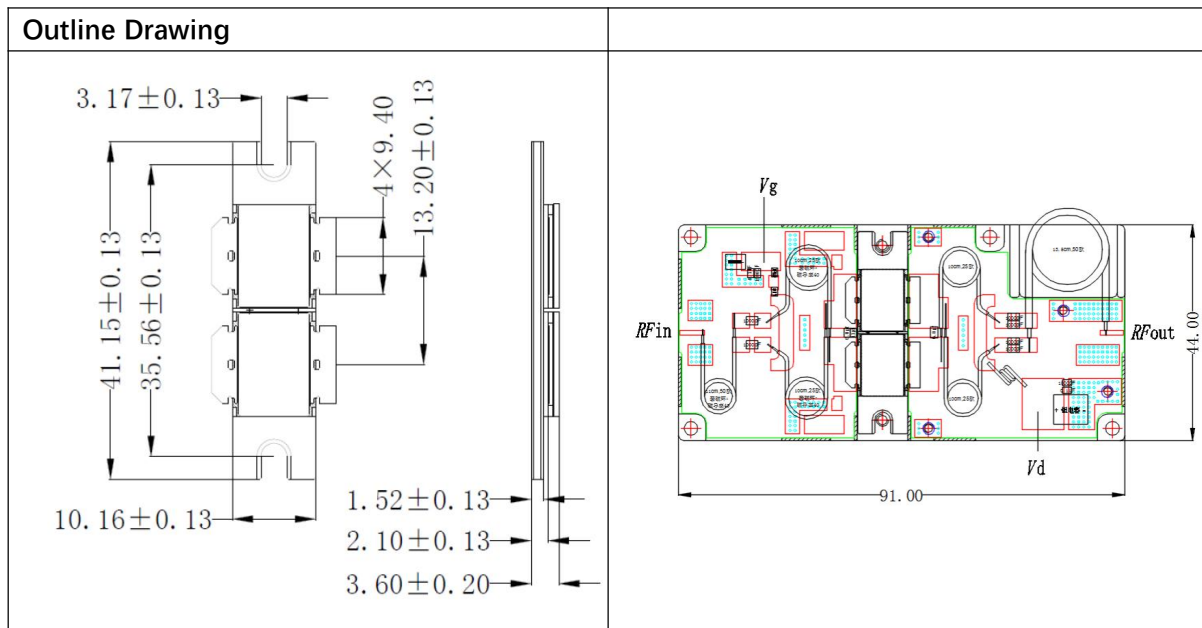


Absolute Max Ratings ($T_A=25^\circ\text{C}$)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	200W	25°C
Tch	Channel Temperature	225°C	【1】
Tm	Mounting Temperature	300°C	1 min, N ₂ Protection
Tstg	Storage Temperature	-55~150°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing



Note:

- (1) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence of this product. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (2) Pay attention to heat dissipation during the use of this product. The higher the shell temperature, the shorter the service life, and the operating temperature should not be higher than 85 degrees;
- (3) This product is an electrostatic sensitive device. It is necessary to pay attention to electrostatic protection during storage and use, and it needs to be well grounded when using it.
- (4) The input standing wave is relatively high, and isolation measures are required at the input end.